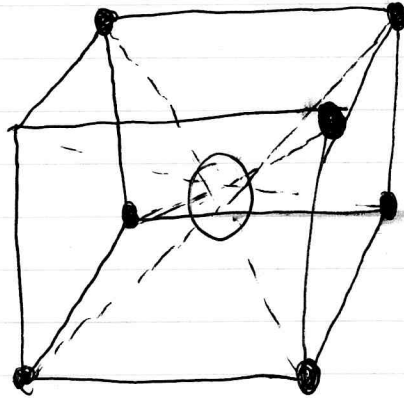


Example: Cesium Chloride crystal structure

(Q): The crystal structure of  $\text{CsCl}$  is shown below. The dark spheres represent atoms of  $\text{Cl}$ .



Identify the crystal system:

(A): Cubic

(Q): Identify the Bravais Lattice:

(A): Simple cubic

(Q): Identify the basis of the crystal structure:

(A):  $\text{Cs}^+ \text{Cl}^-$  pair

### Example: Palladium Structure

- (A):
- Calculate the lattice constant  $a$  in Pd. Use only the information available in the class periodic table, and express your answer in angstroms.
  - Calculate the distance between adjacent (110) planes in palladium (Pd). Hint: Use your work from the first part.

(A): We see of the formula

$$a = \left( \frac{4 \cdot V_{\text{molar}}}{N_{\text{Av}}} \right)^{1/3} = \left( \frac{4 \cdot (8.85 \text{ cm}^3/\text{mol})}{6.022 \cdot 10^{23} \text{ atoms/mol}} \right)^{1/3} = 3.89 \cdot 10^{-8} \text{ cm} = 3.89 \text{ \AA}$$

• We found that  $a = 3.89 \text{ \AA}$ , then since

$$d = \frac{a}{\sqrt{h^2 + k^2 + l^2}}$$

$$d_{(110)} = \frac{3.89 \text{ \AA}}{\sqrt{2}} = 2.79 \text{ \AA}$$

Example: N-type ~~silicon~~ silicon

(Q): • You wish to make n-type silicon. Select all suitable dopant atoms from the following list:

X | P  
| B  
| Mg  
| Ga  
X | As  
| In  
X | Sb  
| Al  
| Ti  
| H

• Name the majority charge carrier in the doped material.

| Holes  
X | Electrons  
| Electron-hole pairs  
| The dopant ion

• The conduction band is at a higher energy than the valence band.

X | True  
| False

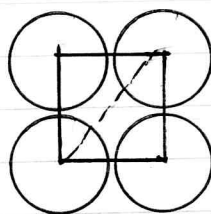
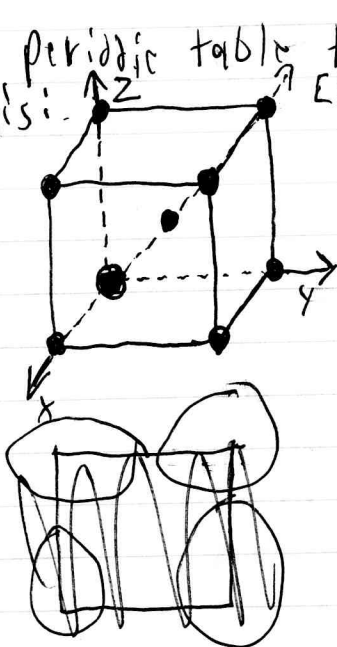
• No electronic states lie between the conduction and valence bands in n-type silicon.

X | True  
| False

## Example: Molybdenum Density

(Q): Calculate the density of atoms along  $[011]$  in Mo. Use only the information provided in your class periodic table and express your answer in units of atoms/cm.

(A): We see by the periodic table that Molybdenum has a BCC structure - we let's draw this:

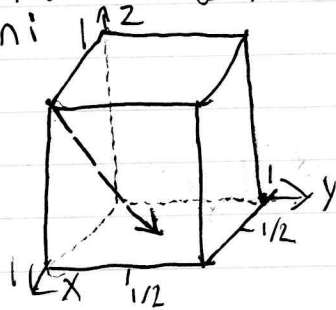


We see by the figures that along the  $[011]$  vector, there are 1 atom every  $\sqrt{2}a$ , this gives

$$\begin{aligned} \frac{1 \text{ atom}}{\sqrt{2}a} &= \frac{1}{\sqrt{2}} \left( \frac{2 \cdot \text{molar volume}}{\text{Avogadro's number}} \right)^{1/3} \\ &= \frac{1}{\sqrt{2}} \left( \frac{2 \cdot 6.022 \cdot 10^{23}}{\text{molar volume}} \right)^{1/3} \\ &= \frac{1}{\sqrt{2}} \left( \frac{2 \cdot \text{molar volume}}{\text{Avogadro's number}} \right)^{1/3} = 2.24 \cdot 10^7 \end{aligned}$$

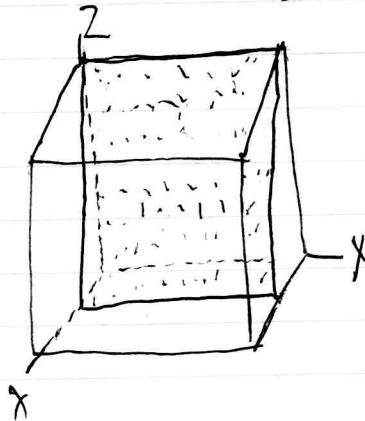
# Example: Directions and planes

(Q): Name the following ~~features~~ crystallographic features below using proper crystallographic notation:



(A):  $[\bar{1} \ 1 \ 2]$

(Q):



(A):  $(201)$

### Example: Structure of CdO

(a): CdO is cubic with a lattice constant  $a = 4.695 \text{ \AA}$  and a density  $\rho = 8.15 \text{ g/cm}^3$ . Determine the crystal structure of CdO.

(A): Recall the formula

$$\frac{x \text{ bases}}{a^3} = \frac{N_A r}{V_{\text{molar}}}$$

and

$$V_{\text{molar}} = \frac{m_a}{\rho}$$

Then,

$$x \text{ bases} = \frac{(4.695 \text{ \AA})^3 \cdot (6.022 \cdot 10^{23}) \cdot (8.15 \text{ g/cm}^3)}{128.4 \text{ g}} = 3.96 \text{ bases}$$

Note that the Face Centered Cubic shape has 4 bases;

$$3.96 \approx 4,$$

thus the CdO has FCC structure

### Example: Free carrier density in Ge

(Q): Chemical analysis of a germanium crystal reveals indium at a level of 0.003091 %. Assuming that the concentration of thermally excited charge carriers from the Ge matrix is negligible, what is the density of free charge carriers (carriers/cm<sup>3</sup>) in this Ge crystal?

(A): ~~Let the volume be 1 cm<sup>3</sup>; let  $\phi = 0.000003091$ ; then the mass of this crystal is~~

$$\phi \cdot 7.31 \text{ g/cm}^3 \cdot 1 \text{ cm}^3 = 2.26 \cdot 10^{-5} \text{ g indium}$$

$$2.26 \cdot 10^{-5} \text{ g} \cdot \frac{1 \text{ mole}}{114.818 \text{ g}} = 1.968 \cdot 10^{-7} \text{ mole} \cdot \frac{6.022 \cdot 10^{23} \text{ carriers}}{\text{mole}}$$

$$= 1.185 \cdot 10^{17} \text{ carriers.}$$

Since we assume a volume of 1 cm<sup>3</sup>, then the carrier density is  
(1.185 · 10<sup>17</sup> carriers/cm<sup>3</sup>)

### Example: Boron doping

(Q): Determine the amount (in grams) of boron that when substantially incorporated into 1 kg of silicon will establish a charge carrier density of  $3.091 \cdot 10^{17}$  carriers/cm<sup>3</sup>.

(A): We see that 1 kg of silicon has volume  $394.85 \text{ cm}^3$ ;

Then we want X grams B such that

$$x \text{ grams B} \cdot \frac{1 \text{ mole}}{10.811 \text{ g}} \cdot \frac{6.022 \cdot 10^{23} \text{ atoms}}{1 \text{ mole}} \stackrel{394.85 \text{ cm}^3}{=} 3.091 \cdot 10^{17} \text{ carriers/cm}^3$$

$$X = 0.00212 \text{ g}$$